



The 1st CSIS International Symposium on Spintronics-based VLSIs

and

The 7th RIEC International Workshop on Spintronics

Date: February 3rd and 4th, 2011

Venue: Laboratory for Nanoelectronics and Spintronics,
4th Floor, Conference Room, Tohoku University,
Sendai, Japan

<http://www.csis.tohoku.ac.jp/>

Symposium Registration

Registration: E-mail to CSIS Support Office (sien@csis.tohoku.ac.jp) by January 17th, 2011.

Symposium Fee: Free

Banquet Registration

Advance Registration: E-mail to CSIS Support Office (sien@csis.tohoku.ac.jp) by January 17th, 2011.

Banquet Fee: 5,000 JPY

Banquet Fee will be collected on site at the Symposium

Sponsors

The symposium and the workshop are sponsored and supported by:

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- Ministry of Education, Culture, Sports, Science & Technology, Japan
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- Tsukuba Innovation Arena for Nanotechnology
- Research Institute of Electrical Communication (RIEC), Tohoku University

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Hideo Ohno (CSIS and RIEC, Tohoku University)

Tetsuo Endoh (CSIS and Center for Interdisciplinary Research, Tohoku University)

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Michihiko Yamanouchi (CSIS, Tohoku University)

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Local Staff

Yutaka Kadowaki (CSIS, Tohoku University)

Noriko Sato (CSIS, Tohoku University)

Manami Abe (CSIS, Tohoku University)

Osamu Sugasawa (CSIS, Tohoku University)

Atsuko Yonezawa (CSIS, Tohoku University)

PROGRAM

Thursday February 3rd, 2011

- Materials and Devices -

Opening 9:00 -9:15		Opening Remarks and Announcements
Invited talk 9:15-9:50	T1	Magnetic tunnel junction based orthogonal spin transfer devices <u>Andrew D. Kent</u> ¹ , Huanlong Liu ¹ , Daniel Bedau ¹ , Jordan Katine ² and Juergen Langer ³ (¹ New York University, ² Hitachi-GST, ³ Singulus Technologies)
Invited talk 9:50-10:25	T2	Materials design and science of magnetic tunnel junctions with perpendicular anisotropy electrodes for VLSIs <u>Shoji Ikeda</u> ^{1,2} , M. Yamanouchi ² , H. Sato ² , K. Miura ^{3,2,1} , K. Mizunuma ¹ , H. Yamamoto ³ , R. Koizumi ¹ , H. D. Gan ² , M. Endo ¹ , S. Kanai ¹ , J. Hayakawa ³ , F. Matsukura ^{1,2} , H. Ohno ^{1,2} (^{1,2} Tohoku University, ³ Hitachi)
10:25-10:45		Coffee Break
Invited talk 10:45-11:20	T3	Multiscale modeling for spintronics <u>Claudia K. A. Mewes</u> , William H. Butler, Tim Mewes (University of Alabama)
Invited talk 11:20-11:55	T4	Self-consistent calculations of spin transport and magnetization dynamics <u>Kyung-Jin Lee</u> ¹ , Hyun-Woo Lee ² , Jung-Hwan Moon ¹ , Seo-Won Lee ¹ , Kyoung-Whan Kim ² (¹ Korea University, ² Pohang University of Science and Technology)
11:55-13:30		Lunch
Invited talk 13:30-14:05	T5	Observation of intrinsic pinning mechanism in current-induced domain wall motion T. Koyama ¹ , D. Chiba ¹ , K. Ueda ¹ , H. Tanigawa ² , S. Fukami ² , T. Suzuki ² , N. Ohshima ² , N. Ishiwata ² , Y. Nakatani ³ , and <u>Teruo Ono</u> ¹ (¹ Kyoto University, ² NEC, ³ University of Electro-communications)
Invited talk 14:05-14:40	T6	Rashba Spin-Orbit torques in ferromagnetic thin films <u>Gilles Gaudin</u> ¹ , I. M. Miron ^{1,2} , T. Moore ^{1,3} , H. Szambolics ¹ , S. Auffret ¹ , B. Rodmacq ¹ , L. D. Buda-Prejbeanu ¹ , A. Schuhl ¹ , S. Pizzini ³ , J. Vogel ³ , M. Bonfim ⁴ , P. Gambardella ^{2,5} (¹ SPINTEC, ² ICN-CSIC, ³ CNRS/UJF, ⁴ Universidade Federal do Paraná, ⁵ ICREA)
Invited talk 14:40-15:15	T7	Universality between current- and field-driven domain wall motion in ferromagnetic metallic nanowires Jae-Chul Lee ^{1,2} , Kab-Jin Kim ¹ , Jisu Ryu ³ , Kyoung-Woong Moon ¹ , Sang-Jun Yun ¹ , Gi-Hong Gim ¹ , Kang-Soo Lee ¹ , Kyung-Ho Shin ² , <u>Hyun-Woo Lee</u> ³ , and Sug-Bong Choe ¹ (¹ Seoul National University, ² KIST, ³ Pohang University of Science and Technology)
15:15-15:35		Coffee Break

Invited talk 15:35-15:55	T8	Domain wall motion cell with perpendicularly magnetized Co/Ni wire for high-speed memory and logic <u>Shunsuke Fukami and N. Ishiwata (NEC)</u>
Invited talk 15:55-16:15	T9	Temperature dependence of domain patterns observed in demagnetized CoFeB/MgO films with perpendicular anisotropy <u>Michihiko Yamanouchi¹, A. Jander^{2,3}, P. Dhagat^{2,3}, S. Ikeda^{1,3}, F. Matsukura^{1,3}, and H. Ohno^{1,3} (¹Tohoku University, ²Oregon State University)</u>
Invited talk 16:15-16:50	T10	NRI Spintronics Research for Beyond CMOS Technology <u>Dejan Markovic (UCLA)</u>
16:55-18:25	POSTER SESSION See pages 5 and 6	
Banquet 18:30-20:30	<i>Katahira Sakura Hall, Tohoku University</i>	

Friday February 4th, 2011

Spintronics-based LSIs

Invited talk 9:00-9:35	F1	Nonvolatile computer systems and memory hierarchy transformation with STT RAM technology <u>Tetsuo Endoh</u> ^{1,2} , S. Ikeda ^{1,3} , T. Hanyu ^{1,4} , N.Kasai ¹ and H.Ohno ^{1,3} (^{1,2,3,4} Tohoku University.)
Invited talk 9:35-10:10	F2	How spintronics and STT-RAM can benefit future mobile applications <u>Nick Yu</u> (Qualcomm)
Invited talk 10:10-10:45	F3	Design considerations and challenges of STT MRAM products R. Beach ¹ , G. Jan ¹ , <u>Po Kang Wang</u> ¹ , D. Tang ¹ , C. Horng ¹ , W. Kula ¹ , T. Torng ¹ , D.C. Worledge ² , J.Z. Sun ² , G. Hu ² , M. C. Gaidis ² , and W. J. Gallagher ² (¹ Magic Technologies, ² IBM)
10:45-11:05	Coffee Break	
Invited talk 11:05-11:40	F4	Advances in materials and structures for STT-RAM <u>Vladimir Nikitin</u> , Dmytro Apalkov, Steven Watts, Alexey Khvalkovskiy, Xueti Tang, Alexander Driskill-Smith, Kiseok Moon, Adrian Ong, Daniel Lottis, Eugene Chen, Mohamad Krounbi (Grandis)
Invited talk 11:40-12:15	F5	High efficient and back hopping free STT writing on perpendicular MTJs <u>Hiroaki Yoda</u> ¹ , N. Shimomura ¹ , T. Kai ¹ , T. Kishi ¹ , H. Aikawa ¹ , M. Yoshikawa ¹ , T. Nagase ¹ , K. Nishiyama ¹ , E. Kitagawa ¹ , T. Daibou ¹ , M. Amano ¹ , S. Takahashi ¹ , M. Nakayama ¹ , S. Ikegawa ¹ , M. Nagamine ¹ , J. Ozeki ¹ , S. Yuasa ² , S. Mizukami ⁶ , Y. Ando ³ , Y. Suzuki ⁴ , Y. Nakatani ⁵ , T. Miyazaki ⁶ , and K. Ando ² (¹ Toshiba, ² AIST, ^{3,6} Tohoku University, ⁴ Osaka University, ⁵ University of Electro-Communications)
12:15-14:00	Lunch	
Invited talk 14:00-14:35	F6	Can the STT-MRAM replace a DRAM ? <u>Kijoon H. P. Kim</u> (Samsung Electronics)
Invited talk 14:35-15:10	F7	Status and outlook of MRAM technology <u>Brad N. Engel</u> , J.M. Slaughter, N.D. Rizzo, F.B. Mancoff, R. Whig, J.J. Sun, K. Smith, K. Nagel, and D. Houssameddine (Everspin Technologies)
Invited talk 15:10-15:45	F8	MTJ-based nonvolatile logic-in-memory architecture and its applications <u>Takahiro Hanyu</u> ^{1,2} , S. Matsunaga ¹ , D. Suzuki ¹ , M. Natsui ^{1,2} , S. Ikeda ^{1,3} , T. Endoh ^{1,4} , and H. Ohno ^{1,3} (^{1,2,3,4} Tohoku University)
Closing 15:45-15:50		Closing Remarks

Thursday February 3rd, 2011

POSTER SESSION 16:55-18:25

P1	Band structure and magneto- transport properties in II-VI nanostructures semiconductors. Application to infrared detector superlattices Abdelhakim Nafidi (University Ibn Zohr)
P2	Dependence of the exchange bias direction on the cooling-field strength Jangyup Son, Soogil Lee, Sanghoon Kim, and Jongill Hong (Yonsei University)
P3	Spin-transfer-torque dependence on MgO tunnel barrier thickness in MTJs W. Skowroński ¹ , T. Stobiecki ¹ , J. Wrona ¹ , G. Reiss ² , K. Chalapat ³ , G. S. Paraoanu ³ , and S. van Dijken ⁴ (¹ AGH University of Science and Technology, ² Bielefeld University, ^{3,4} Aalto University)
P4	Development of reconfigurable spin logic block based on SpRAM for 3D-stacked reconfigurable spin processor R. Nakazawa, H. Kino, K. Kiyoyama, T. Tanaka, and M. Koyanagi (Tohoku University)
P5	A post oxidation process of Mg layer for MgO barrier magnetic tunnel junctions H. Yamamoto ¹ , K. Ono ¹ , T. Morita ¹ , S. Ikeda ² , and H. Ohno ² (¹ ULVAC, ² Tohoku University)
P6	Structural and magnetic properties of Fe- and Mn-doped Si thin films Jooyoung Suh ¹ , Sang Woo Pak ¹ , Kyung Su Lee ¹ , Eun Kyu Kim ^{1*} , and Yoon Shon ² (¹ Hanyang University, ² Dongguk University)
P7	Well-width dependence of spin relaxation in InGaAs quantum wells Y. Kunihashi ¹ , M. Kohda ^{1,2} , and J. Nitta ¹ (¹ Tohoku University, ² PRESTO JST)
P8	Fabrication of PbPd_{1-x}Co_xO₂ spin gapless semiconductor films and investigation of their magnetic and transport properties Y. F. Chiang ² , H . L. Su ^{1,3} , S. Y. Huang ¹ , and J. C. A. Huang ^{1,2} (^{1,2} National Cheng Kung University, ³ Hefei University of Technology)
P9	Electron wave packet dynamics in the spin torque transfer Mitsuhiro Arikawa ^{1,2} , Yasuhiro Hatsugai ³ , and Kenji Shiraishi ³ (^{1,3} University of Tsukuba, ² CREST)
P10	Exchange biased magnetic tunnel junctions with thin CoFeB electrodes for in-plane and out-of-plane magnetic field sensing P. Wiśniowski ¹ , J. Wrona ¹ , W. Skowroński ¹ , T. Stobiecki ¹ , S. Cardoso ² , and P. Freitas ² (¹ AGH University of Science and Technology, ² INESC-MN and IN-Institute of Nanoscience and Nanotechnology)
P11	Gilbert magnetic damping constant of Co-based Heusler alloy thin films M. Oogane ¹ , T. Kubota ¹ , Y. Kota ¹ , S. Mizukami ² , H. Naganuma ¹ , A. Sakuma ¹ and Y. Ando ¹ (^{1,2} Tohoku University)

P12	MgO magnetic tunnel junctions with a synthetic free layer consisting of CoFeB/Ru/ perpendicular magnet Yeon Sub Lee ^{1,3} , Byoung-Chul Min ^{*1} , Gyung Min Choi ¹ , Jürgen Langer ² , Berthold Ocker ² , Wolfram Maass ² , Young Keun Kim ³ , and Kyung-Ho Shin ¹ (¹ KIST, ² Singulus Technologies, ³ Korea University)
P13	Exchange bias of multiferroic BiFeO₃ epitaxial films Hiroshi Naganuma, Mikihiko Oogane, and Yasuo Ando (Tohoku University)
P14	Spin torque diode effect of magnetic tunnel junction with synthetic ferrimagnetic free layer Nobuhito Inami ¹ , Hiroshi Naganuma ¹ , Mikihiko Oogane ¹ , Yasuo Ando ¹ , Shoji Ikeda ^{2,3} , and Hideo Ohno ^{2,3} (^{1,2,3} Tohoku University)
P15	Current driven domain wall dynamics in perpendicularly magnetized ultrathin CoFeB nanowires Masamitsu Hayashi ¹ , Jaivardhan Sinha ¹ , Carsen Kline ¹ and Seiji Mitani ¹ Shunsuke Fukami ² , and Nobuyuki Ishiwata ² (¹ NIMS, ² NEC)
P16	Influences of Boron composition on tunnel magnetoresistance properties of double-MgO-barrier magnetic tunnel junctions H. D. Gan ¹ , S. Ikeda ^{1,2} , M. Yamanochi ¹ , K. Mizunuma ² , K. Miura ^{3,1,2} , F. Matsukura ^{1,2} , and H. Ohno ^{1,2} (^{1,2} Tohoku University)
P17	Annealing effect on perpendicular magnetic anisotropy of CoFeB/MgO structure H. Sato ¹ , R. Koizumi ² , M. Yamanouchi ¹ , S. Ikeda ^{1,2} , K. Miura ^{1,2,3} , K. Mizunuma ² , H. D. Gan ¹ , F. Matsukura ^{1,2} and H. Ohno ^{1,2} (^{1,2} Tohoku University, ³ Hitachi)
P18	Annealing stability for tunnel magnetoresistance in MgO-CoFeB based magnetic tunnel junctions with perpendicular anisotropy CoFe/Pd multilayers Kotaro Mizunuma ¹ , Michihiko Yamanouchi ² , Shoji Ikeda ^{1,2} , Hideo Sato ² , Hiroyuki Yamamoto ³ , Hua-Dong Gan ² , Katsuya Miura ^{3,1,2} , Jun Hayakawa ³ , Fumihiro Matsukura ^{1,2} , and Hideo Ohno ^{1,2} (^{1,2} Tohoku University, ³ Hitachi)
P19	Modulation of magnetic anisotropy in Ta/Co₄₀Fe₄₀B₂₀/MgO by electric fields: thickness and annealing temperature dependences S. Kanai ¹ , M. Endo ¹ , S. Ikeda ^{1,2} , F. Matsukura ^{1,2} , H. Ohno ^{1,2} (^{1,2} Tohoku University)
P20	Buffer layer dependence of magnetic domain wall creep in (Ga,Mn)As A. Suzuki ¹ , A. Kanda ¹ , F. Matsukura ^{1,2} , H. Ohno ^{1,2} (^{1,2} Tohoku University)
P21	MTJ edge deformation influence on switching current distribution for a shaped-varying MTJ switched with magnetic field H. Honjo S. Saito , R. Nebashi, N. Sakimura, S. Miura*, and T. Sugabayashi (NEC)
P22	Chemical modification of magnetic thin film during alcohol-based plasma etching Keizo Kinoshita, K. Suemitsu, N. Ohshima, N. Ishiwata, T. Sugabayashi (NEC)